

Features

Field Stop Trench gate IGBT、Low Collector-Emitter saturation voltage、High short circuit capability
Low switching losses

Version

STD

Application

Industrial Motor Drivers, Inverter, Welding, UPS

Status

Mass production

Specifications

Gate-Emitter voltage VCES [V]	Collector current IC [A]	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C typical limit	Collector- Emitter saturation voltage VCE(sat) @Tj=25deg C upper limit	Gate Voltage VGES [V]	Gate-Emitter threshold voltage VGE(th) lower limit [V]	Gate-Emitter threshold voltage VGE(th) upper limit [V]
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MMJ65A0F00xx

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		[V]	[V]			
650	100	1.45	1.75	-30~30	5.20	6.60
Internal gate resistor Rgint typical limit [Ω]		Die size X [mm]	Die size Y [mm]		Junction temperature Tj [deg.C]	
1.7		6.00	9.00		-40~175	